

Highly stable and efficient photoelectrochemical water oxidation at an anisotropically crystallized monoclinic WO₃ film with predominant growth of (202) plane

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An anisotropically crystallized monoclinic WO₃ films were synthesized on fluorine-doped tin oxide (FTO) electrode by a one-step hydrothermal method using oxalic acid (Oxa) as a structure directing agent. The WO₃ film (denoted as WO₃(w-Oxa)) prepared with Oxa was composed of relatively large layered-sheets with 2 ~ 5 μm length with predominant growth of the (202) plane (parallel to the substrate), in contrast to small layered-sheets with 1 ~ 2 μm length with predominant growths (020) or (200) planes for the WO₃(w/o-Oxa) film prepared without Oxa. Although the photocurrents were generated above 0.6 V vs. RHE for WO₃(w-Oxa) and WO₃(w/o-Oxa) electrodes, the incident photon to electron conversion efficiency (IPCE₄₂₀ = 38%) at 420 nm and 1.23 V vs RHE for the former was 2.7 times higher than that (14%) of the latter. The higher IPCE₄₂₀ for the WO₃(w-Oxa) is ascribed to higher charge separation ($\eta_{\text{sep}} = 50\%$) and catalytic ($\eta_{\text{cat}} = 95\%$) efficiencies compared to those ($\eta_{\text{sep}} = 19\%$ and $\eta_{\text{cat}} = 82\%$) for the WO₃(w/o-Oxa) electrode. The photoelectrochemical impedance spectroscopic (PEIS) measurement suggested effective bulk charge transport in the WO₃(w-Oxa) electrode compared to the WO₃(w/o-Oxa) electrode, which works to the advantage of suppressed recombination of photogenerated charges (electrons and holes), being responsible for the higher η_{sep} , eventually causing the higher IPCE for the WO₃(w-Oxa) electrode. The WO₃(w-Oxa) electrode showed the high photocurrent stability (95% remain for 7 h) and Faraday efficiency (FE_{O₂}) of 95% for water oxidation. The high stability and FE_{O₂} of the WO₃(w-Oxa) electrode result from the suppression of the competed photo-oxidation of the surface by the attenuated hole accumulation due to efficient water oxidation at the (202) facet surface.